

FMSBSS123-H

List

List.....1

Features.....2

Package outline.....2

Mechanical data.....2

Maximum ratings2

Electrical characteristics.....3

Rating and characteristic curves.....4

Pinning information.....5

Marking.....5

Suggested solder pad layout.....5

Packing information.....6

Reel packing.....7

Suggested thermal profiles for soldering processes.....7

High reliability test capabilities.....8

FMSBSS123-H

170mA 100V N-Channel Enhancement Mode MOSFET

Features

- Low on-resistance $R_{DS(ON)} \leq 6 \Omega$, @ $V_{GS}=10V$, $I_D=170mA$.
 $R_{DS(ON)} \leq 10 \Omega$, @ $V_{GS}=4.5V$, $I_D=170mA$.
- Low input capacitance : typ 29pF.
- Fast switching speed : typ 8ns.
- Low output capacitance : Max=15pF.
- Low threshold : max 2.0V.
- Lead-free parts meet RoHS requirements.

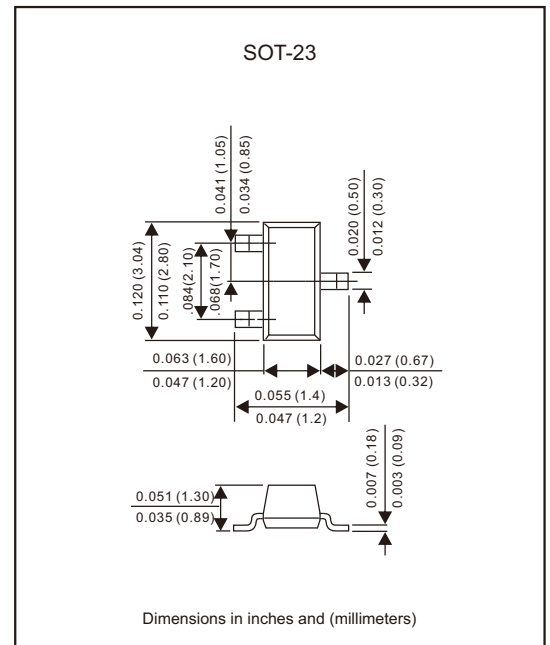
Applications

- TrenchFET Power MOSFET
- Load Switch for Portable Devices.
- DC/DC Converter.

Mechanical data

- Epoxy:UL94-V0 rated flame retardant.
- Case : Molded plastic, SOT-23.
- Terminals : Solder plated, solder able per MIL-STD-750, Method 2026.
- Weight : Approximated 8mg.

Package outline



Maximum Ratings (At $T_A=25^\circ C$ Unless otherwise noted)

Parameter	Symbol	Rating	Unit
Drain source voltage	V_{DS}	100	V
Gate source voltage	V_{GS}	± 20	V
Drain current continuous (Note 1)	I_D	170	mA
Pulsed drain current ($t_p=10\mu s$)	I_{DM}	680	mA
Power Dissipation	P_D	350	mW
Thermal resistance, junction to ambient	$R_{\theta JA}$	357	$^\circ C/W$
Operating junction temperature range	T_J	+150	$^\circ C$
Storage temperature range	T_{STG}	-50 to +150	$^\circ C$

FMSBSS123-H

Electrical characteristics (At $T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Static parameters						
Drain-source breakdown voltage	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	BV_{DSS}	100			V
Drain-source leakage current	$V_{DS}=100\text{V}$, $V_{GS}=0\text{V}$	I_{DSS}			1.0	μA
Gate-source leakage current	$V_{GS}=\pm 20\text{V}$, $V_{DS}=0\text{V}$	I_{GSS}			± 50	nA
Gate threshold voltage(Note 3)	$V_{DS}=V_{GS}$, $-I_D=250\mu\text{A}$ (Note 3)	$V_{GS(TH)}$	1.0	1.7	2.0	V
Static drain-source on-state resistance (Note 3)	$V_{GS}=10\text{V}$, $I_D=170\text{mA}$	$R_{DS(ON)}$			6.0	Ω
	$V_{GS}=4.5\text{V}$, $I_D=170\text{mA}$				10	
Forward Transconductance(Note 3)	$V_{DS}=10$, $I_D=170\text{mA}$ (Note 3)	g_{fs}	80			mS

Dynamic parameters

Input capacitance	$V_{GS}=0\text{V}$, $V_{DS}=25\text{V}$, $f=1.0\text{MHz}$	C_{iss}		29	60	pF
Out capacitance		C_{oss}		10	15	
Reverse transfer capacitance		C_{rss}		2.0	6.0	

Switching parameters

Total gate charge	$V_{GS}=10\text{V}$, $V_{DS}=10\text{V}$, $I_D=0.22\text{A}$	Q_g		1.4	2.0	nC
Gate to source charge		Q_{gs}		0.15	0.25	
Gate to drain charge		Q_{gd}		0.2	0.4	
Turn-on delay time	$V_{DS}=30\text{V}$, $V_{GS}=10\text{V}$, $R_G=50\Omega$, $I_D=0.28\text{A}$	$t_{d(on)}$		8		ns
Rise time		t_r		13		
Turn-off delay time		$t_{d(off)}$		8		
Fall time		t_f		16		

Source-drain diode ratings and characteristics

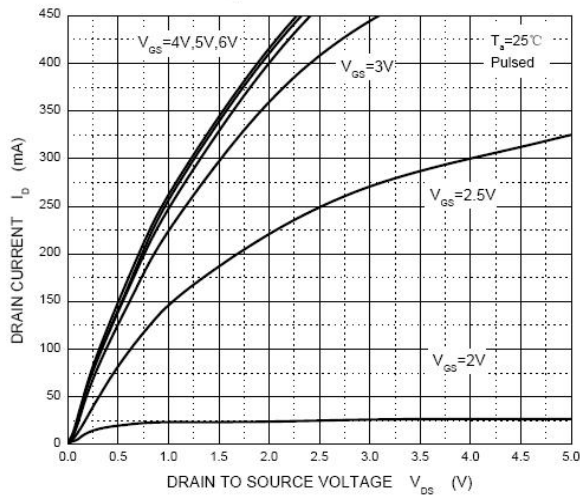
Drain-source diode forward voltage	$I_{SD}=0.34\text{A}$, $V_{GS}=0\text{V}$	V_{SD}			1.3	V
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- Notes : 1. Surface mounted on FR4 board using the minimum recommended pad size.
2. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
3. Switching characteristics are independent of operating junction temperature.
4. Guaranteed by design, not subject to producing.

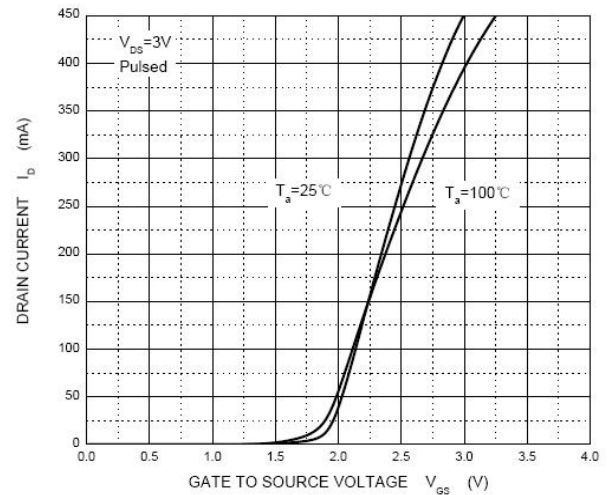
FMSBSS123-H

Rating and characteristic curves

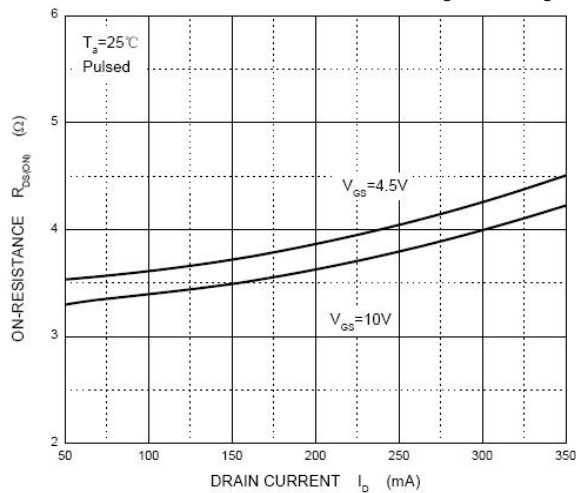
Output characteristics



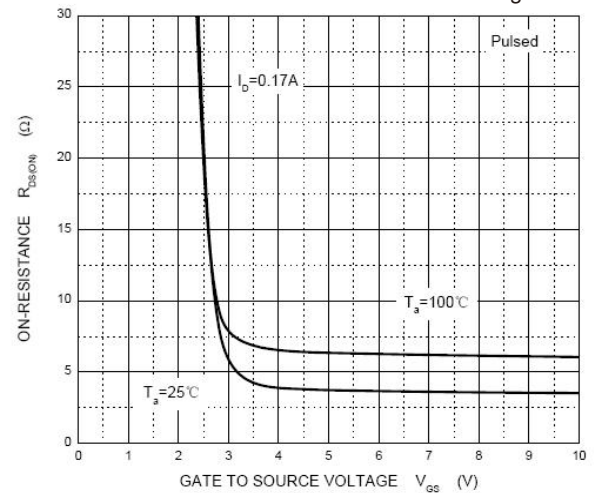
Transfer characteristics



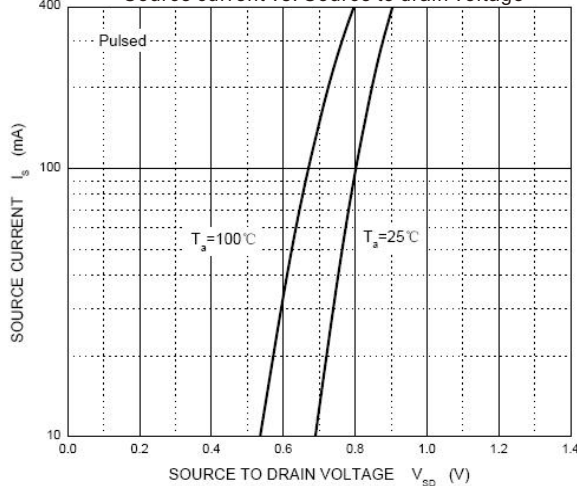
On-resistance vs. Drain current and gate voltage



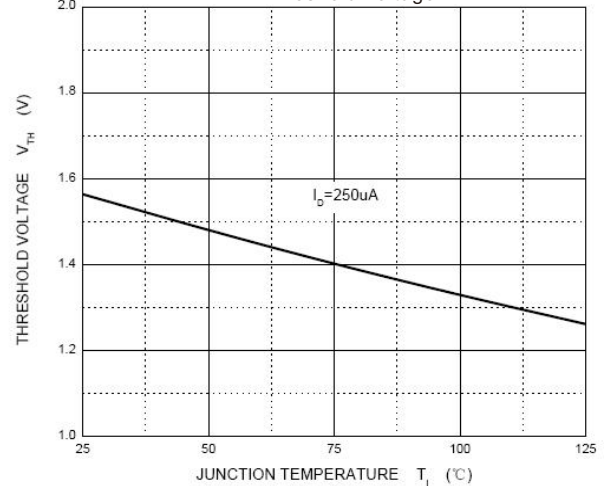
On-resistance vs. Gate to source voltage



Source current vs. Source to drain voltage

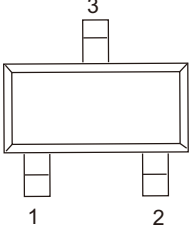
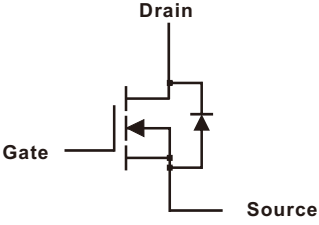


Threshold Voltage



FMSBSS123-H

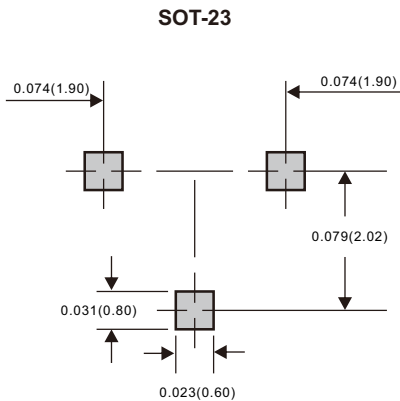
Pinning information

Pin	Simplified outline	Symbol
Pin 1 Gate Pin 2 Source Pin 3 Drain		

Marking

Type number	Marking code
FMSBSS123	SA, B123

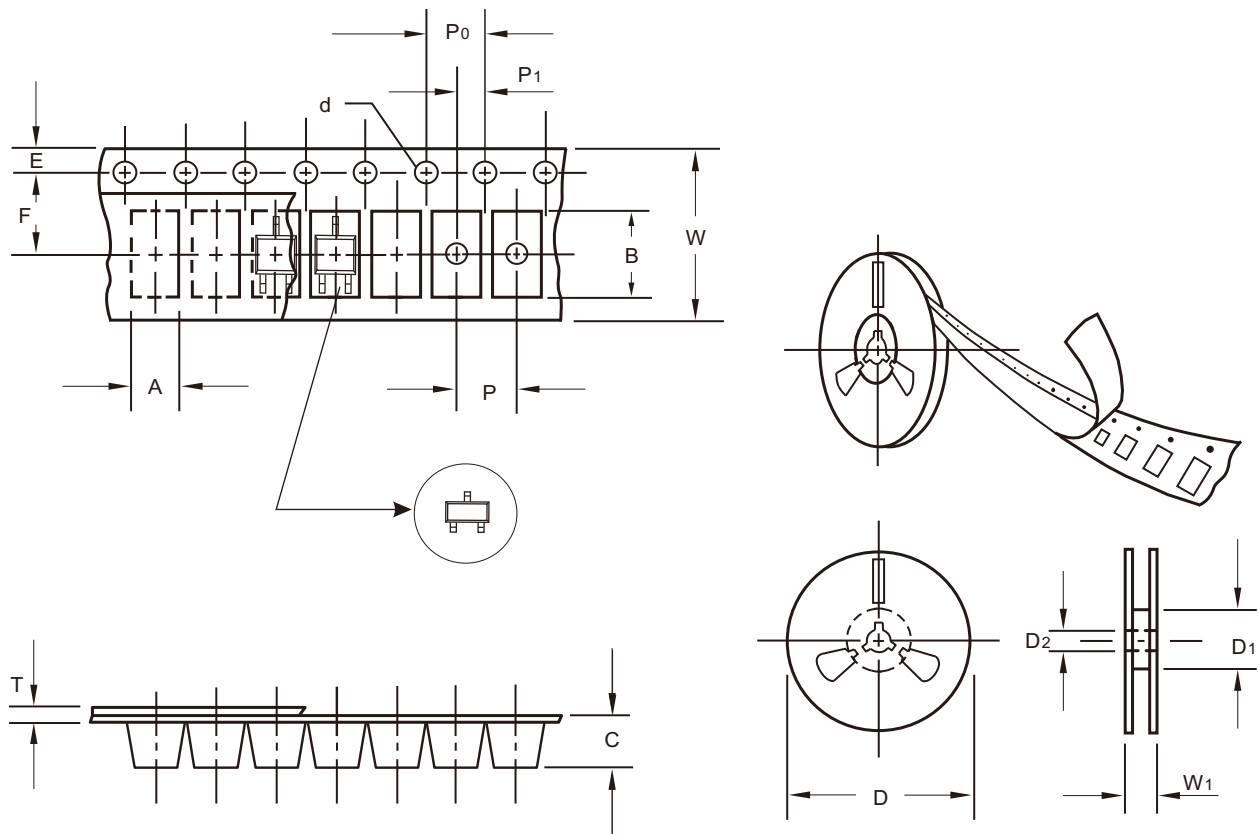
Suggested solder pad layout



Dimensions in inches and (millimeters)

FMSBSS123-H

Packing information



unit:mm

Item	Symbol	Tolerance	SOT-23
Carrier width	A	0.1	3.15
Carrier length	B	0.1	2.77
Carrier depth	C	0.1	1.22
Sprocket hole	d	0.1	1.50
13" Reel outside diameter	D	2.0	-
13" Reel inner diameter	D1	min	-
7" Reel outside diameter	D	2.0	178.00
7" Reel inner diameter	D1	min	55.00
Feed hole diameter	D2	0.5	13.00
Sprocket hole position	E	0.1	1.75
Punch hole position	F	0.1	3.50
Punch hole pitch	P	0.1	4.00
Sprocket hole pitch	P0	0.1	4.00
Embossment center	P1	0.1	2.00
Overall tape thickness	T	0.1	0.23
Tape width	W	0.3	8.00
Reel width	W1	1.0	12.0

Note: Devices are packed in accordance with EIA standard RS-481-A and specifications listed above.

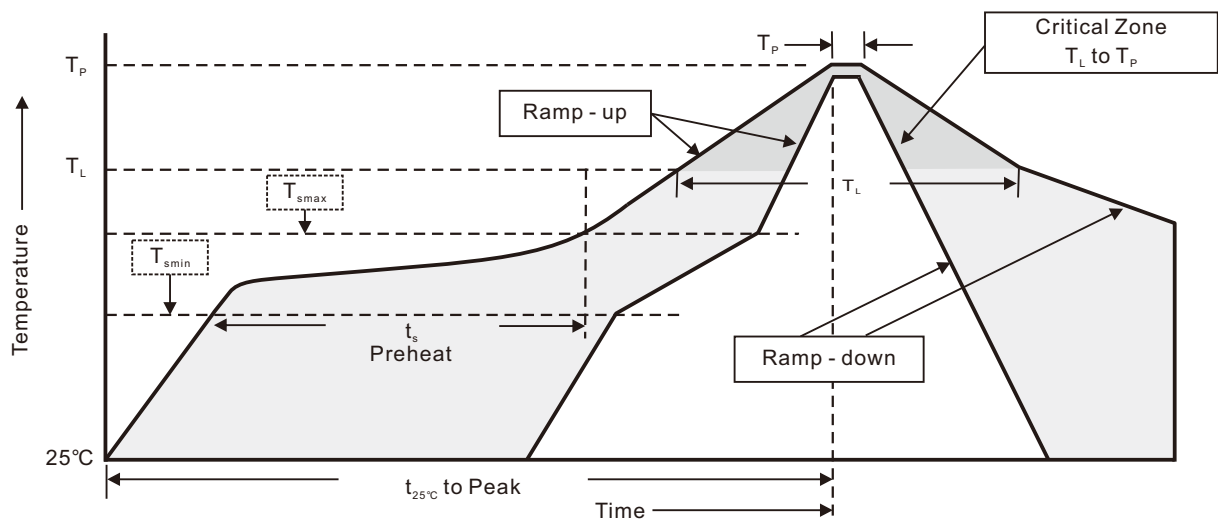
FMSBSS123-H

Reel packing

PACKAGE	REEL SIZE	REEL (pcs)	COMPONENT SPACING (m/m)	BOX (pcs)	INNER BOX (m/m)	REEL DIA, (m/m)	CARTON SIZE (m/m)	CARTON (pcs)	APPROX. GROSS WEIGHT (kg)
SOT-23	7"	3,000	4.0	30,000	183*123*183	178	382*257*387	240,000	11.6

Suggested thermal profiles for soldering processes

- Storage environment : Temperature = 5°C ~ 40°C, Humidity = 55%, ±25%.
- Reflow soldering of surface - Mount devices.



3. Reflow soldering

Profile feature	Soldering condition
Average ramp-up rate (T_L to T_p)	< 3 °C/sec
Preheat - Temperature Min (T_{smin}) - Temperature Max (T_{smax}) - Time (Min to Max) (t_s)	150°C 200°C 60 ~ 120 sec
T_{smax} to T_L - Ramp-up rate	< 3 °C / sec
Time maintained above : - Temperature (T_L) - Time (T_L)	217°C 60 ~ 260 sec
Peak temperature (T_p)	255 °C -0 / +5°C
Time with 5°C of actual peak temperature (T_p)	10 ~ 30 sec
Ramp-down rate	< 6°C / sec
Time 25°C to peak temperature	< 6 minutes